L Number	Hits	Search Text	DB	Time stamp
15	7	(boe or buffer\$3 near2 oxid\$2 near2 etch\$4) same ("h.sub.2so.sub.4" or h2s04 or sulfuric) same combination	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/28 10:25
16	90	(boe or buffer\$3 near2 oxid\$2 near2 etch\$4) same ("h.sub.2so.sub.4" or h2s04 or sulfuric)	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/07/28 10:26
17	20	(boe or buffer\$3 near2 oxid\$2 near2 etch\$4) same ("h.sub.2so.sub.4" or h2s04 or sulfuric) same (HF)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/07/28 10:32
_	118	(contact near5 plug same (silicon or si) and temperature near3 (deposit\$4 or grow\$4) near10 (silicon or si)) and (lpcvd or low near2 pressure near2 chemical near2 vapor)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/04 16:19
-	14		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/04 16:37
_	84	selectiv\$4 near3 epitax\$4 near10 (silicon or si or polysilicon) and (low near2 pressure near3 chemical near2 vapor or lpcvd) and two near10 (deposit\$4 or grow\$4 or epitax\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/04 16:51
_	38	((silicon or si) near4 amorphous or polysilicon) same plug near5 contact same (low near4 pressure or lpcvd) same temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/04
_	24	((silicon or si) near4 amorphous or polysilicon) near10 plug near5 contact same (low near4 pressure or lpcvd) same temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/04 17:00
-	81	contact near5 plug same (single or epitax\$4) near5 (si or silicon) same (amorphous near4 (silicon) or poly or poly\$1si or poly\$1silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/05 14:59
-	40	(contact near5 plug same (single or epitax\$4) near5 (si or silicon) same (amorphous near4 (silicon) or poly or poly\$1si or poly\$1silicon)) and (lpcvd or low near3 pressure near3 chemical near2 vapor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/05 15:18
_	10	• · ·	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/05 15:51
-	53		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/05 15:55
-	18	(lpcvd or low near3 pressure near3 chemical near2 vapor) and contact near4 plug near10 (silicon or si) and flow near3 rate same temperature same silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/05 15:56

-	58	(lpcvd or low near2 pressure near2	USPAT;	2003/06/05
		chemical) near10 (silicon or si) same	US-PGPUB;	16:24
		plug same temperature	EPO; JPO;	i
			DERWENT; IBM TDB	
		(1	USPAT;	2003/06/05
-	3	(lpcvd or low near2 pressure near2 chemical) near10 (silicon or si) near10	US-PGPUB;	16:26
		(crystal\$4 or crystallin\$4) same plug	EPO; JPO;	10.20
		same temperature	DERWENT;	
		Same temperature	IBM TDB	
_	62	(lpcvd or low near2 pressure near2	USPAT;	2003/06/05
	"-	chemical) near10 (silicon or si) near10	US-PGPUB;	16:26
		(crystal\$4 or crystallin\$4) same	EPO; JPO;	
		temperature	DERWENT;	
		•	IBM TDB	
-	6	(lpcvd or low near2 pressure near2	USPĀT;	2003/06/05
[chemical) near10 (silicon or si) near10	US-PGPUB;	16:31
		(crystal\$4 or crystallin\$4) near10	EPO; JPO;	
		select\$5 same temperature	DERWENT;	1
			IBM_TDB	
-	28	` 	USPAT;	2003/06/05
1		chemical) same (silicon or si) near10	US-PGPUB;	16:35
1		(crystal\$4 or crystallin\$4) near10	EPO; JPO;	
		select\$5 same temperature	DERWENT;	
1		(1	IBM_TDB	2002/06/05
-	84		USPAT;	2003/06/05 16:57
1		chemical) and (silicon or si) near10	US-PGPUB; EPO; JPO;	10.37
		(crystal\$4 or crystallin\$4) near10	DERWENT;	
		select\$5 near4 (epitax\$4 or grow\$4 or deposit\$4) same temperature	IBM TDB	
1_	56		USPAT;	2003/06/06
-	30	or "o.sub.2") near5 plasma same clean\$4	US-PGPUB;	10:22
		or organiz , nears prusma same creany:	EPO; JPO;	10.22
			DERWENT;	
			IBM TDB	
_	5	(NF3 or "NF.sub.3") near10 (o2 or oxygen	USPAT;	2003/06/06
		or "o.sub.2") near5 plasma same clean\$4	US-PGPUB;	11:10
		same (contact or plug)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	4	clean\$4 same (contact or plug) same (boe	USPĀT;	2003/06/06
		or buffer\$3 near2 oxid\$2 near2 etch\$4)	US-PGPUB;	09:43
		same ("h.sub.2so.sub.4" or h2s04 or	EPO; JPO;]
		sulfuric)	DERWENT;	
		1	IBM_TDB	2002/07/22
-	30	clean\$4 same (boe or buffer\$3 near2	USPAT;	2003/07/28
1		oxid\$2 near2 etch\$4) same ("h.sub.2so.sub.4" or h2s04 or sulfuric)	US-PGPUB; EPO; JPO;	10:18
1		(n.sub.250.5ub.4 of n2504 of suffuric)	DERWENT;	
1			IBM TDB	
1_		 wet near4 etch\$4 same (dry or plasma)	USPAT;	2003/06/06
1		near3 etch\$4 same clean\$4 same (contact	US-PGPUB;	09:49
		or plug or via) same (NF3 or "nf.sub.3")	EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	9	wet near4 etch\$4 same (dry or plasma)	USPAT;	2003/06/06
1		near3 etch\$4 same clean\$4 same (contact	US-PGPUB;	09:50
1	1	or plug or via) same bak\$4	EPO; JPO;	
1			DERWENT;	
			IBM_TDB	
-	25		USPAT;	2003/06/06
		or "o.sub.2") near5 plasma) and (boe or	US-PGPUB;	09:53
ĺ		buffer\$3 near2 oxid\$3 near3 etch\$4)	EPO; JPO;	
1			DERWENT;	
		//	IBM_TDB	2002/06/06
_	128		USPAT;	2003/06/06
		etch\$4) same (h2so4 or "h.sub.2so.sub.4"	US-PGPUB;	09:59
1		or sulfur\$3)	EPO; JPO; DERWENT;	
1			IBM TDB	
	1		TOT IDD	L

-	18	((boe or buffer\$3 near2 oxid\$3 near3	USPAT;	2003/06/06 09:57
		etch\$4) same (h2so4 or "h.sub.2so.sub.4" or sulfur\$3)) same (contact or via or	US-PGPUB; EPO; JPO;	09.57
		plug or trench)	DERWENT;	
			IBM_TDB	
-	34	(boe or buffer\$3 near2 oxid\$3 near3	USPAT;	2003/06/06
		etch\$4) same (h2so4 or "h.sub.2so.sub.4"	US-PGPUB;	10:00
		or sulfur\$3) same clean\$4	EPO; JPO;	
*			DERWENT; IBM TDB	
_	39	(NF3 or "NF.sub.3" or fluor\$4) near10 (o2	USPAT;	2003/06/06
	35	or oxygen or "o.sub.2") near5 (plasma or	US-PGPUB;	10:52
		dry) same clean\$4 same (via or hole or	EPO; JPO;	
		contact or plug or trench)	DERWENT;	
			IBM_TDB	2002/06/06
-	95	((NF3 or "NF.sub.3" or fluor\$4) near10	USPAT; US-PGPUB;	2003/06/06 10:54
		(o2 or oxygen or "o.sub.2") near5 (plasma or dry) same clean\$4 and (via or hole or	EPO; JPO;	10.54
		contact or plug or trench)) not ((NF3 or	DERWENT;	
		"NF.sub.3" or fluor\$4) near10 (o2 or	IBM TDB	
	•	oxygen or "o.sub.2") near5 (plasma or	_	
		dry) same clean\$4 same (via or hole or		
		contact or plug or trench)) not (((NF3 or		
		"NF.sub.3") near10 (o2 or oxygen or		
		"o.sub.2") near5 plasma) and (boe or buffer\$3 near2 oxid\$3 near3 etch\$4))		
_	71	((NF3 or "NF.sub.3" or fluor\$4) near10	USPAT;	2003/06/06
	, 1	(o2 or oxygen or "o.sub.2") near5 (plasma	US-PGPUB;	10:54
		or dry) same clean\$4 and (via or hole or	EPO; JPO;	
•		contact or plug or trench)) not ((NF3 or	DERWENT;	
		"NF.sub.3" or fluor\$4) near10 (o2 or	IBM_TDB	
		oxygen or "o.sub.2") near5 (plasma or		
		<pre>dry) same clean\$4 same (via or hole or contact or plug or trench)) not (((NF3 or</pre>		
		"NF.sub.3") near10 (o2 or oxygen or		
		"o.sub.2") near5 plasma) and (boe or		
		buffer\$3 near2 oxid\$3 near3 etch\$4)) not		
		((NF3 or "NF.sub.3") near10 (o2 or oxygen		
	7.1	or "o.sub.2") near5 plasma same clean\$4)	HCDAT.	2003/06/06
_	71	((NF3 or "NF.sub.3" or fluor\$4) near10 (o2 or oxygen or "o.sub.2") near5 (plasma	USPAT; US-PGPUB;	10:56
		or dry) same clean\$4 and (via or hole or	EPO; JPO;	1
		contact or plug or trench)) not ((NF3 or	DERWENT;	
		"NF.sub.3" or fluor\$4) near10 (o2 or	IBM_TDB	
		oxygen or "o.sub.2") near5 (plasma or		
		dry) same clean\$4 same (via or hole or		
		contact or plug or trench)) not (((NF3 or "NF.sub.3") near10 (o2 or oxygen or		
		"o.sub.2") near5 plasma) and (boe or		
		buffer\$3 near2 oxid\$3 near3 etch\$4)) not		
		((NF3 or "NF.sub.3") near10 (o2 or oxygen		
1		or "o.sub.2") near5 plasma same clean\$4)		
		not (clean\$4 same (boe or buffer\$3 near2		
		oxid\$2 near2 etch\$4) same ("h.sub.2so.sub.4" or h2s04 or sulfuric))		
	51	(wet same (dry or plasma) same clean\$4	USPAT;	2003/06/06
	"	same etch\$4 same (via or hole or contact	US-PGPUB;	11:02
		or plug or residu\$4)).ab.	EPO; JPO;	
1			DERWENT;	
1		((1772) 1772 - 211)	IBM_TDB	2002/06/06
-	113	((NF3 or "NF.sub.3") near10 (o2 or oxygen or "o.sub.2") near5 plasma same etch\$4)	USPAT; US-PGPUB;	2003/06/06 11:34
		not ((NF3 or "NF.sub.3") near10 (o2 or	EPO; JPO;	11.51
		oxygen or "o.sub.2") near5 plasma same	DERWENT;	
1	1	clean\$4)	IBM_TDB	
-	38	(NF3 or "Nf.sub.3" or fluor\$4) near20 (02	USPAT;	2003/06/09
1	1	or "o.sub.2" or oxygen) near5 plasma same	US-PGPUB;	15:27
	1	(clean\$4) same (via or contact or hole or	EPO; JPO;	
	1	trench)	DERWENT; IBM TDB	
L	<u> </u>	<u></u>	םמד זימד [

Continue	
Clean\$4 Clea	
DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB U	
S5 dry near10 wet same bak\$4 same clean\$4 SART; US-FGPUB; EPO; JPO; DERWENT; IBM TDB cetch\$4) SART; US-FGPUB; EPO; JPO; DERWENT; IBM TDB cetch\$4] SART; US-FGPUB; IPM TDB cetch\$4] SART; US-	
S5	
US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; USPAT; US-PGPUB; USPAT; US-PGPUB; USPAT; US-PGPUB; USPAT; US-PGPUB; US-PGPUB; USPAT; US-PGPUB; US-PGPU	
- 22 (sulfuric or "H.sub.25o.sub.4" or h2so4) near10 (boe or buffer\$3 near2 oxide near2 etch\$4) - 22 (sulfuric or "H.sub.25o.sub.4" or h2so4) near10 (boe or buffer\$3 near2 oxid\$3 near2 etch\$4) - 24 (sulfuric or "H.sub.25o.sub.4" or h2so4) near10 (boe or buffer\$3 near2 oxid\$3 near2 etch\$4) - 94 (sulfuric or "H.sub.25o.sub.4" or h2so4) same (boe or buffer\$3 near2 oxid\$3 near2 etch\$4) - 30 (sulfuric or "H.sub.25o.sub.4" or h2so4) same (boe or buffer\$3 near2 oxid\$3 near2 etch\$4) same clean\$4 - 35 (sulfuric or "H.sub.25o.sub.4" or h2so4) same (boe or buffer\$3 near2 oxid\$3 near2 etch\$4) same clean\$4 - 8 (sulfuric or "H.sub.25o.sub.4" or h2so4) same (boe or buffer\$3 near2 oxid\$3 near2 etch\$4) and ("nf3" or "nf.sub.3" or nitrogen near2 fluoride) - 23 clean\$4 same (wet or acid) same (dry or plasma) same (bak\$4) same semiconduct\$4 - 50 wet near10 clean\$4 same plug same dry - 50 wet near10 clean\$4 same ("h.sub.2so.sub.4" or h2so4) same (boe or buffer\$3 near2 oxid\$3 near2 etch\$4) and ("nf3" or "nf.sub.3" or nitrogen near2 fluoride) - 50 wet near10 clean\$4 same plug same dry - 50 wet near10 clean\$4 same ("h.sub.2so.sub.4" or h2so4) same (boe or buffer\$3 near2 oxid\$3 near2 etch\$4) and ("nf3" or "nf.sub.3" or nitrogen near2 fluoride) - 50 wet near10 clean\$4 same plug same dry - 50 wet near10 clean\$4 same ("h.sub.2so.sub.4" or h2so4 or sulfuric) - 50 wet near10 clean\$4 same ("h.sub.2so.sub.4" or h2so4 or sulfuric) - 50 wet near10 clean\$4 same ("h.sub.2so.sub.4" or h2so4 or sulfuric) - 50 wet near10 clean\$4 same ("b.sub.2so.sub.4" or h2so4 or sulfuric) - 50 wet near10 clean\$4 same ("b.sub.2so.sub.4" or h2so4 or sulfuric) - 50 wet near10 clean\$4 same ("b.sub.2so.sub.4" or h2so4 or sulfuric) - 50 wet near10 clean\$4 same ("b.sub.2so.sub.4" or h2so4 or sulfuric)	
- 22 (sulfuric or "H.sub.25o.sub.4" or h2so4) near10 (boe or buffer\$3 near2 oxide near2 etch\$4) - 22 (sulfuric or "H.sub.25o.sub.4" or h2so4) near10 (boe or buffer\$3 near2 oxid\$3 near2 etch\$4) - 24 (sulfuric or "H.sub.25o.sub.4" or h2so4) near2 etch\$4) - 35 (sulfuric or "H.sub.25o.sub.4" or h2so4) same (boe or buffer\$3 near2 oxid\$3 near2 etch\$4) - 36 (sulfuric or "H.sub.25o.sub.4" or h2so4) same (boe or buffer\$3 near2 oxid\$3 near2 etch\$4) - 37 (sulfuric or "H.sub.25o.sub.4" or h2so4) same (boe or buffer\$3 near2 oxid\$3 near2 etch\$4) - 38 (sulfuric or "H.sub.25o.sub.4" or h2so4) same (boe or buffer\$3 near2 oxid\$3 near2 etch\$4) same clean\$4 - 38 (sulfuric or "H.sub.25o.sub.4" or h2so4) same (boe or buffer\$3 near2 oxid\$3 near2 etch\$4) and ("nf3" or "nf.sub.3" or nitrogen near2 fluoride) - 23 clean\$4 same (wet or acid) same (dry or plasma) same (bak\$4) same semiconduct\$4 - 23 clean\$4 same (wet or acid) same (dry or plasma) same (bak\$4) same semiconduct\$4 - 30 wet near10 clean\$4 same plug same dry - 31 wet near10 clean\$4 same ("h.sub.2so.sub.4" or h2so4) spar; spar	
Comparison	
22 (sulfuric or "H.sub.2so.sub.4" or h2so4) near10 (boe or buffer\$3 near2 oxide near2 USPĀT; CO03/06/09 18:15	
near10 (boe or buffer\$3 near2 oxide near2 US-PGPUB; etch\$4) 18:15	
etch\$4)	
DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; IS:53 EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; IS:53 EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; IT:49 EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; IT:58	
Comparison	
Comparison	
near10 (boe or buffer\$3 near2 oxid\$3 US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; USPAT; US-PGPUB; US-P	
near2 etch\$4)	
DERWENT; IBM TDB USPAT; US-PGPUB; etch\$4) - 30 (sulfuric or "H.sub.2So.sub.4" or h2so4) same (boe or buffer\$3 near2 oxid\$3 near2 etch\$4) - 30 (sulfuric or "H.sub.2So.sub.4" or h2so4) same (boe or buffer\$3 near2 oxid\$3 near2 etch\$4) same clean\$4 - 8 (sulfuric or "H.sub.2So.sub.4" or h2so4) same (boe or buffer\$3 near2 oxid\$3 near2 etch\$4) same (boe or buffer\$3 near2 oxid\$3 near2 etch\$4) and ("nf3" or "nf.sub.3" or nitrogen near2 fluoride) - 23 clean\$4 same (wet or acid) same (dry or plasma) same (bak\$4) same semiconduct\$4 - 50 wet near10 clean\$4 same plug same dry wet near10 clean\$4 same ("h.sub.2so.sub.4" or h2so4 or sulfuric) wet near10 clean\$4 same ("h.sub.2so.sub.4" or h2so4 or sulfuric) year plasma; perwent; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; I7:49 EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; I7:58	
Sulfuric or "H.sub.2So.sub.4" or h2so4 same (boe or buffer\$3 near2 oxid\$3 near2 US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; I	
Same (boe or buffer\$3 near2 oxid\$3 near2 US-PGPUB; EPO; JPO; DERWENT; IBM TDB US-PGPUB; EP	
etch\$4) - 30 (sulfuric or "H.sub.2So.sub.4" or h2so4) same (boe or buffer\$3 near2 oxid\$3 near2	
etch\$4	
Solution	
- 30 (sulfuric or "H.sub.2So.sub.4" or h2so4) same (boe or buffer\$3 near2 oxid\$3 near2 etch\$4) same clean\$4	
Same (boe or buffer\$3 near2 oxid\$3 near2 US-PGPUB; etch\$4) same clean\$4 US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; etch\$4) and ("nf3" or "nf.sub.3" or nitrogen near2 fluoride) DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; I7:49 USPĀT; US-PGPUB; I7:58 USPĀT; US-PGPUB; USP	
etch\$4) same clean\$4 EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; Etch\$4) and ("nf3" or "nf.sub.3" or nitrogen near2 fluoride) DERWENT; IBM_TDB US-PGPUB; Etch\$4) and ("nf3" or "nf.sub.3" or nitrogen near2 fluoride) DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; USPAT; US-PGPUB; USPAT; US-PGPUB; USPAT; US-PGPUB; USPAT; US-PGPUB; USPAT; US-PGPUB; US	
Solution	
Solution	
Sulfuric or "H.sub.2So.sub.4" or h2so4) USPAT; 2003/06/09 18:33	
Same (boe or buffer\$3 near2 oxid\$3 near2 US-PGPUB; etch\$4) and ("nf3" or "nf.sub.3" or nitrogen near2 fluoride) DERWENT; IBM_TDB TDB US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; IT:49 US-PGPUB; IT:49 US-PGPUB; IT:49 US-PGPUB; IT:58 US-PGPUB;	
etch\$4) and ("nf3" or "nf.sub.3" or nitrogen near2 fluoride) 23 clean\$4 same (wet or acid) same (dry or plasma) same (bak\$4) same semiconduct\$4 - 50 wet near10 clean\$4 same plug same dry - 33 wet near10 clean\$4 same (real or base) 34 wet near10 clean\$4 same (real or base) 35 wet near10 clean\$4 same (real or base) 36 wet near10 clean\$4 same (real or base) 37 wet near10 clean\$4 same (real or base) 38 wet near10 clean\$4 same (real or base) 39 wet near10 clean\$4 same (real or base) 2003/07/16 wash.250.500.500.500.500.500.500.500.500.500	
nitrogen near2 fluoride DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; USPAT; US-PGPUB; I7:58	
- 23 clean\$4 same (wet or acid) same (dry or plasma) same (bak\$4) same semiconduct\$4 USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; IT:58	,
- 23 clean\$4 same (wet or acid) same (dry or plasma) same (bak\$4) same semiconduct\$4 USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; USPAT; US-PGPUB; USPAT; US-PGPUB; US-PG	
plasma) same (bak\$4) same semiconduct\$4 US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; IMM_TDB US-	
EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; US-PGPUB; I7:58	
- 50 wet near10 clean\$4 same plug same dry wet near10 clean\$4 same plug same dry IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; IBM_TDB USPAT; US-PGPUB; 17:49 2003/07/16 US-PGPUB; 17:58	
- 50 wet near10 clean\$4 same plug same dry USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; USPAT; ("h.sub.2so.sub.4" or h2so4 or sulfuric) US-PGPUB; 17:58	
US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; 2003/07/16 ("h.sub.2so.sub.4" or h2so4 or sulfuric) US-PGPUB; 17:58	
EPO; JPO; DERWENT; IBM_TDB 33 wet near10 clean\$4 same ("h.sub.2so.sub.4" or h2so4 or sulfuric) US-PGPUB; 17:58	
DERWENT; IBM_TDB USPAT; ("h.sub.2so.sub.4" or h2so4 or sulfuric) DERWENT; IBM_TDB USPAT; US-PGPUB; 17:58	
33 wet near10 clean\$4 same	
- 33 wet near10 clean\$4 same USPAT; 2003/07/16 ("h.sub.2so.sub.4" or h2so4 or sulfuric) US-PGPUB; 17:58	
("h.sub.2so.sub.4" or h2so4 or sulfuric) US-PGPUB; 17:58	l
1	
I land dry hearto creans and pass and laro, aro, I	
contact DERWENT;	
IBM TDB	l
- 1 shin.in. and contact same clean\$4 and wet USPAT; 2003/07/16	
and dry and bak\$4 US-PGPUB; 18:02	
EPO; JPO;	
DERWENT;	
IBM_TDB	
- 1 shin.in. and contact same clean\$4 same USPAT; 2003/07/16	
"H.sub.2so.sub.4"	
EPO; JPO;	
DERWENT;	l
IBM_TDB USDATE: 2003/07/16	
- 9 shin.in. and contact same clean\$4 same USPAT; 2003/07/16 wet US-PGPUB; 18:11	
wet	l
DERWENT;	
IBM TDB	
- 27 ((("nf.sub.3" or nf3) or Nitrogen near2 USPAT; 2003/07/16	
trifluoride) near30 clean\$4) same US-PGPUB; 18:29	
(contact or via or trench\$4) same plasma EPO; JPO;	
same (oxygen or o2 or "o.sub.2") DERWENT;	
IBM TDB	

-	2	2000100749.pn.	USPAT;	2003/07/16
		•	US-PGPUB;	18:34
			EPO; JPO;	
			DERWENT;	
	0.5		IBM_TDB	2002/07/16
-	85	(contact or via or trench) near20 clean\$4	USPAT;	2003/07/16
		same (combinat\$4 or combin\$4) near10 (dry	US-PGPUB;	18:41
		or plasma)	EPO; JPO;	
1			DERWENT;	
	4.0	1	IBM_TDB	2002/07/16
-	40	(contact or via or trench) near20 clean\$4	USPAT;	2003/07/16
		same (combinat\$4) near10 (dry or plasma)	US-PGPUB;	18:43
			EPO; JPO; DERWENT;	
1			IBM TDB	
	27	(silicon or si) near4 (single or	USPAT;	2003/07/17
-	37	(Silicon or Si) hear4 (Single of	US-PGPUB;	16:53
		epitax\$4) same plug same (lpcvd or low	EPO; JPO;	16:55
	1	near4 pressur\$4)	DERWENT;	
			IBM TDB	
_	28	(silicon or si) near4 (single or	USPAT;	2003/07/17
-	48	epitax\$4) near20 selectiv\$5 same (lpcvd	US-PGPUB;	17:07
	1	or low near4 pressur\$4) near10	EPO; JPO;	1,.0,
		temperature	DERWENT;	
		cemberacare	IBM TDB	
_	14	(silicon or si) near4 (single or	USPAT;	2003/07/18
1		epitax\$4) near20 selectiv\$5 same (lpcvd	US-PGPUB;	10:39
		or low near4 pressur\$4) near20 torr	EPO; JPO;	10.33
		of low heart pressurer, hearzo corr	DERWENT;	
			IBM TDB	
_	15	(silicon or si) near4 (single or	USPAT;	2003/07/18
		epitax\$4) same (lpcvd) near20 torr	US-PGPUB;	10:42
		opiount, sumo (ipova, nomino tota	EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	9	(lpcvd).ti. and silicon near5 (epitax\$4	USPAT;	2003/07/18
		or grow\$4 or deposit\$4) same torr	US-PGPUB;	11:01
			EPO; JPO;	
1			DERWENT;	
			IBM_TDB	
-	15	(seg or selective near2 epitax\$4) near15	USPAT;	2003/07/18
		(si or silicon) same (contact or plug or	US-PGPUB;	11:11
		via) and (h2 or "h.sub.2" or hydrogen)	EPO; JPO;	
		near5 bak\$4	DERWENT;	
			IBM_TDB	0000 (00 / 5 5
-	8	combinat\$4 near10 wet near10 dry near10	USPAT;	2003/07/18
		bak\$4	US-PGPUB;	11:12
	1		EPO; JPO;	
	1		DERWENT;	,
		//haké4 on annosié4 on manis assura	IBM_TDB	2003/07/10
-	9	((bak\$4 or anneal\$4 or rapid near3 thermal or heat near2 treat\$4 or rta or	USPAT; US-PGPUB;	2003/07/18 11:17
	1	rtp or ptp) near25 (hydrogen or h2 or	EPO; JPO;	11.1/
		"h.sub.2")) near30 combinat\$4 near20	DERWENT;	
		clean\$4	IBM TDB	
l _	5	((bak\$4 or anneal\$4 or rapid near3	USPAT;	2003/07/18
]	thermal or heat near2 treat\$4 or rta or	US-PGPUB;	11:18
		rtp or ptp) near25 (hydrogen or h2 or	EPO; JPO;	
		"h.sub.2")) near30 combinat\$4 same	DERWENT;	
]	(contact or plug)	IBM TDB	
-	41	((bak\$4 or anneal\$4 or rapid near3	USPAT;	2003/07/18
]	thermal or heat near2 treat\$4 or rta or	US-PGPUB;	11:19
	j	rtp or ptp) near25 (hydrogen or h2 or	EPO; JPO;	
		"h.sub.2")) near30 (contact or plug) same	DERWENT;	
		plasma	IBM_TDB	
-	2	6111277.pn.	USPAT;	2003/07/18
			US-PGPUB;	13:01
			EPO; JPO;	
]		DERWENT;	
I]		IBM TDB	

_	17	(silicon or si) near10 (select\$4 or	USPAT;	2003/07/18
		selectiv\$4) near5 (epitax\$4 or grow\$4 or	US-PGPUB;	13:17
		deposit\$4) near30 (cone or conical or	EPO; JPO;	
		pyramid\$4)	DERWENT;	
		l	IBM_TDB	0000 (07 (10
-	93		USPAT;	2003/07/18
		selectiv\$4) near30 (cone or conical or	US-PGPUB;	13:15
		pyramid\$4)	EPO; JPO;	
			DERWENT;	
		l	IBM_TDB	0000/07/10
-	76	((silicon or si) near10 (select\$4 or	USPAT;	2003/07/18
		selectiv\$4) near30 (cone or conical or	US-PGPUB;	13:15
		pyramid\$4)) not ((silicon or si) near10	EPO; JPO;	
		(select\$4 or selectiv\$4) near5 (epitax\$4	DERWENT;	
		or grow\$4 or deposit\$4) near30 (cone or	IBM_TDB	
		conical or pyramid\$4))	***********	2002/07/10
-	8		USPAT;	2003/07/18
		selectiv\$4) near5 (epitax\$4 or grow\$4 or	US-PGPUB;	17:10
		deposit\$4) near30 (peak)	EPO; JPO;	
			DERWENT;	
	105		IBM_TDB USPAT;	2003/07/18
-	105	carrier near5 gas\$4 near20 smooth		
			US-PGPUB;	17:25
			EPO; JPO; DERWENT;	
	10	(IBM_TDB USPAT;	2003/07/18
-	10	'	USPAT; US-PGPUB;	17:24
		CVD	EPO; JPO;	17:24
			DERWENT;	
			IBM TDB	
	7	(carrier near5 gas\$4 near20 smooth) same	USPAT;	2003/07/18
_	. '	chemical near3 vapor near2 deposit\$4	US-PGPUB;	17:24
	<u> </u>	Chemical hears vapor hearz depositor	EPO; JPO;	17.23
			DERWENT;	
	1		IBM TDB	
_	17	carrier near5 gas\$4 near20 smooth near4	USPAT;	2003/07/18
	'	flow and CVD	US-PGPUB;	17:27
		TIOW WITH CVD	EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	68	CVD same Process near5 parameter near10	USPAT;	2003/07/18
		flow near4 rate	US-PGPUB;	17:33
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	13	LPCVD same Process near5 parameter near10	USPAT;	2003/07/18
		flow near4 rate	US-PGPUB;	17:35
			EPO; JPO;	
			DERWENT;	
	1		IBM_TDB	
-	34	LPCVD same parameter near10 flow near4	USPĀT;	2003/07/18
1	1	rate	US-PGPUB;	18:31
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	10		USPĀT;	2003/07/18
		sulfuric) near20 clean\$4) same (buffer\$4	US-PGPUB;	18:55
		near2 oxide or boe)	EPO; JPO;	
			DERWENT;	
L			IBM TDB	